

# MMBT2907AL, SMMBT2907AL

## General Purpose Transistors

### PNP Silicon

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-60	Vdc
Collector-Base Voltage	$V_{CBO}$	-60	Vdc
Emitter-Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current - Continuous	$I_C$	-600	mAdc
Collector Current - Peak (Note 3)	$I_{CM}$	-1200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation - FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation - Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Total Device Dissipation - Heat Spreader or equivalent, (Note 4) @ $T_A = 25^\circ\text{C}$	$P_D$	350	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

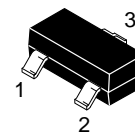
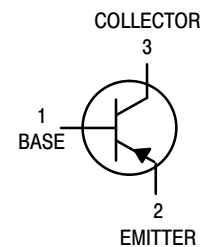
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
3. Reference SOA curve.
4. Heat Spreader or equivalent =  $450 \text{ mm}^2$ , 2 oz.



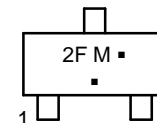
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SOT-23 (TO-236AB)  
CASE 318  
STYLE 6

#### MARKING DIAGRAM



2F = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT2907ALT1G SMMBT2907ALT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2907ALT3G SMMBT2907ALT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage (Note 5) ( $I_C = -1.0\text{ mAdc}$ , $I_B = 0$ ) ( $I_C = -10\text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-60 -60	-	Vdc
Collector-Base Breakdown Voltage ( $I_C = -10\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-60	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E = -10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CE} = -30\text{ Vdc}$ , $V_{EB(off)} = -0.5\text{ Vdc}$ )	$I_{CEX}$	-	-50	nAdc
Collector Cutoff Current ( $V_{CB} = -50\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = -50\text{ Vdc}$ , $I_E = 0$ , $T_A = 125^\circ\text{C}$ )	$I_{CBO}$	-	-0.010 -10	$\mu\text{Adc}$
Base Cutoff Current ( $V_{CE} = -30\text{ Vdc}$ , $V_{EB(off)} = -0.5\text{ Vdc}$ )	$I_{BL}$	-	-50	nAdc

## ON CHARACTERISTICS

DC Current Gain ( $I_C = -0.1\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -1.0\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -10\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -150\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -500\text{ mAdc}$ , $V_{CE} = -10\text{ Vdc}$ ) (Note 5)	$h_{FE}$	75 100 100 100 50	-	-
Collector-Emitter Saturation Voltage (Note 5) ( $I_C = -150\text{ mAdc}$ , $I_B = -15\text{ mAdc}$ ) (Note 5) ( $I_C = -500\text{ mAdc}$ , $I_B = -50\text{ mAdc}$ )	$V_{CE(sat)}$	-	-0.4 -1.6	Vdc
Base-Emitter Saturation Voltage (Note 5) ( $I_C = -150\text{ mAdc}$ , $I_B = -15\text{ mAdc}$ ) ( $I_C = -500\text{ mAdc}$ , $I_B = -50\text{ mAdc}$ )	$V_{BE(sat)}$	-	-1.3 -2.6	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (Notes 5, 6), ( $I_C = -50\text{ mAdc}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	200	-	MHz
Output Capacitance ( $V_{CB} = -10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	-	8.0	pF
Input Capacitance ( $V_{EB} = -2.0\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	-	30	pF

## SWITCHING CHARACTERISTICS

Turn-On Time	$(V_{CC} = -30\text{ Vdc}$ , $I_C = -150\text{ mAdc}$ , $I_{B1} = -15\text{ mAdc}$ )	$t_{on}$	-	45	ns
Delay Time		$t_d$	-	10	
Rise Time		$t_r$	-	40	
Turn-Off Time	$(V_{CC} = -6.0\text{ Vdc}$ , $I_C = -150\text{ mAdc}$ , $I_{B1} = I_{B2} = -15\text{ mAdc}$ )	$t_{off}$	-	100	
Storage Time		$t_s$	-	80	
Fall Time		$t_f$	-	30	

5. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

6.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

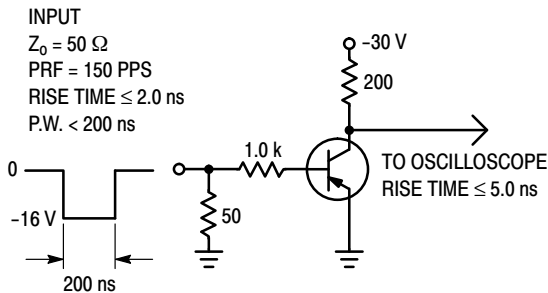


Figure 1. Delay and Rise Time Test Circuit

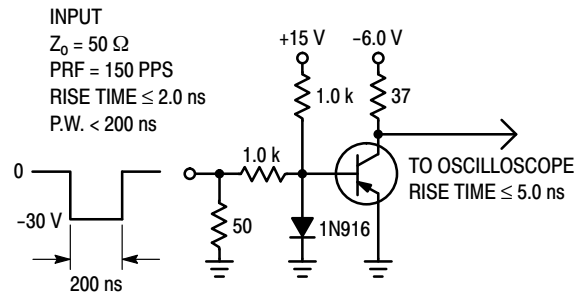


Figure 2. Storage and Fall Time Test Circuit

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## TYPICAL CHARACTERISTICS



Figure 3. DC Current Gain



Figure 4. Collector Saturation Region

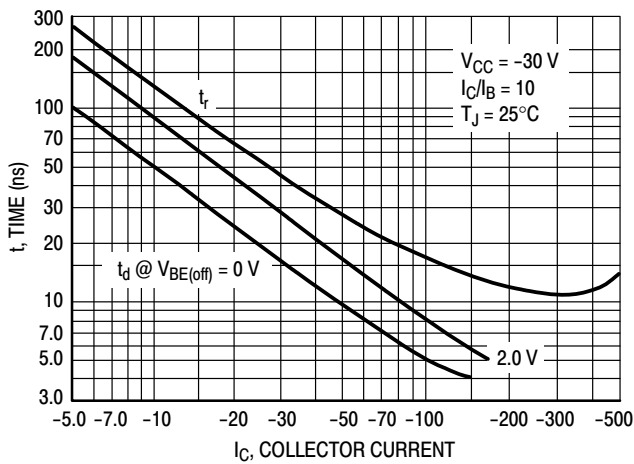


Figure 5. Turn-On Time

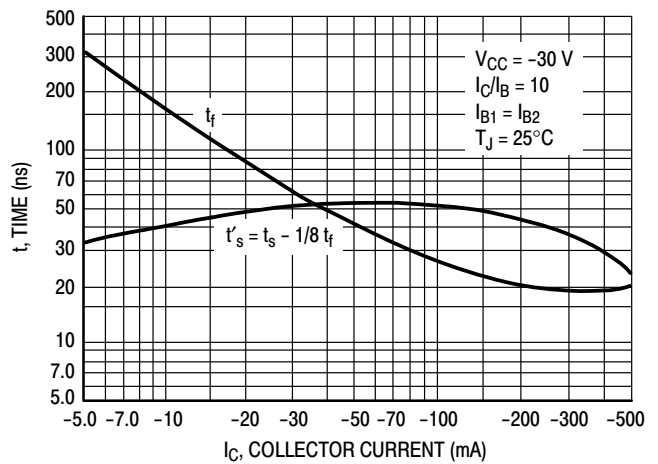


Figure 6. Turn-Off Time

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## TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$

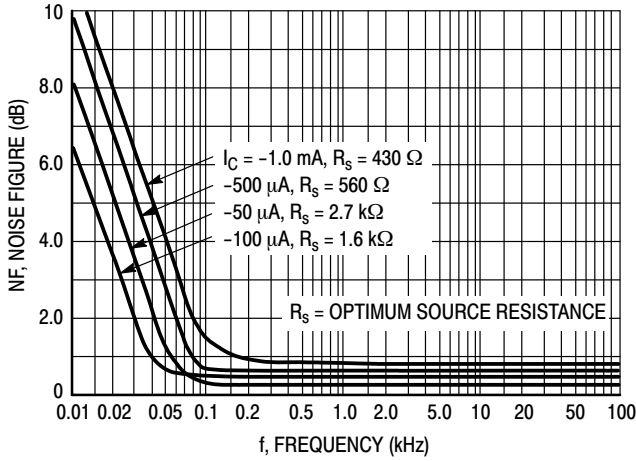


Figure 7. Frequency Effects

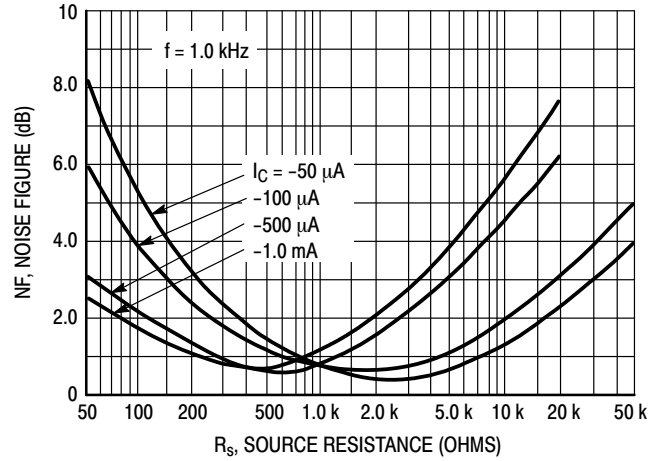


Figure 8. Source Resistance Effects

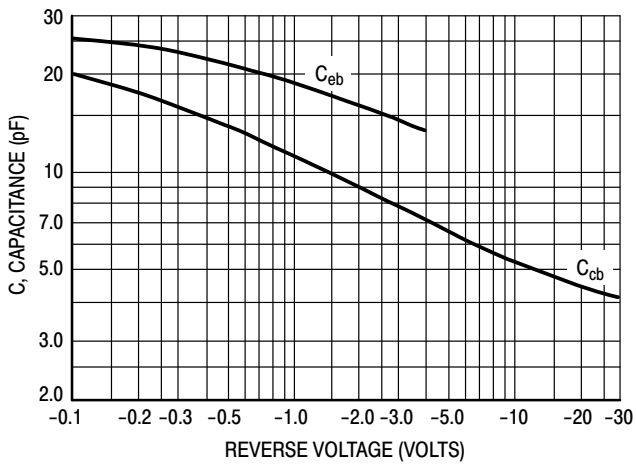


Figure 9. Capacitances

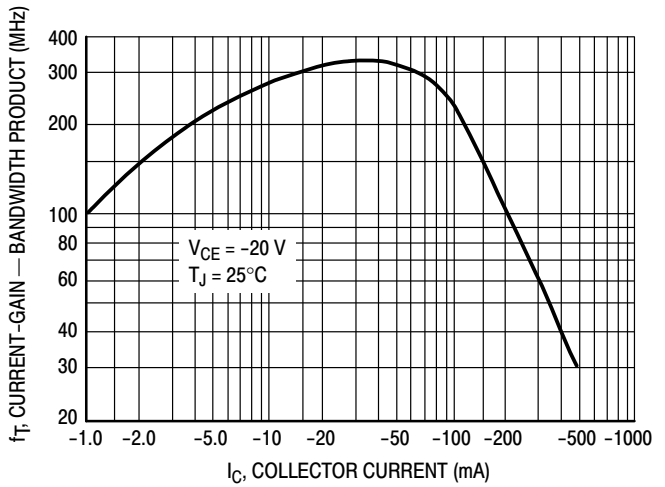


Figure 10. Current-Gain - Bandwidth Product

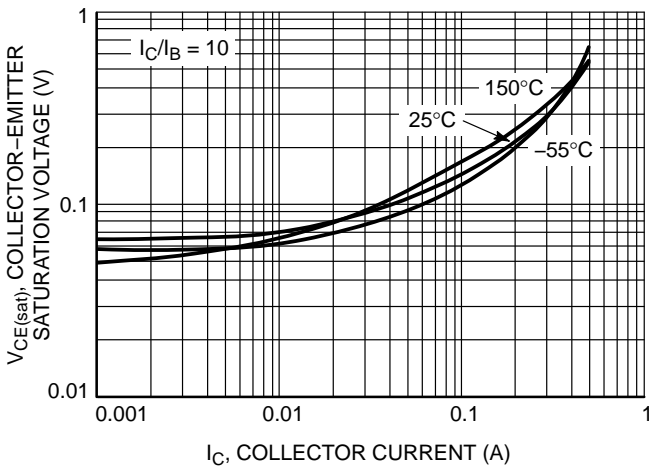


Figure 11. Collector-Emitter Saturation Voltage vs. Collector Current

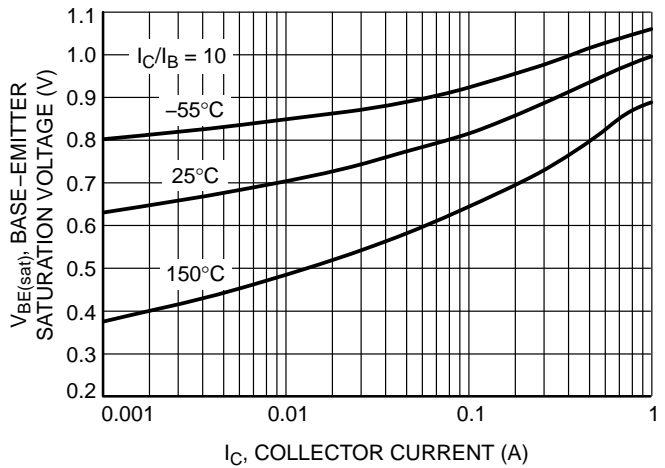


Figure 12. Base-Emitter Saturation Voltage vs. Collector Current

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## TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$

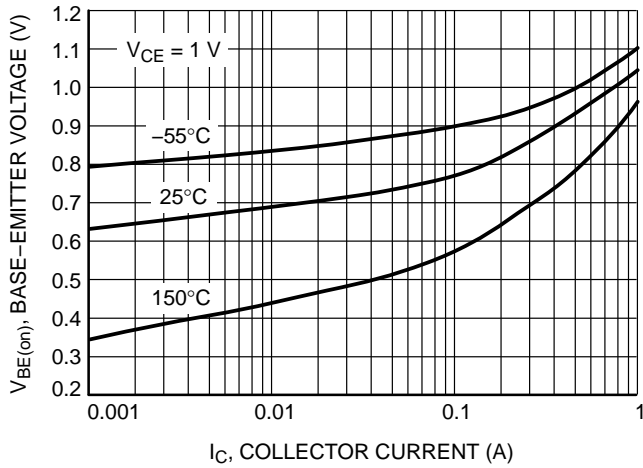


Figure 13. Base Emitter Voltage vs. Collector Current

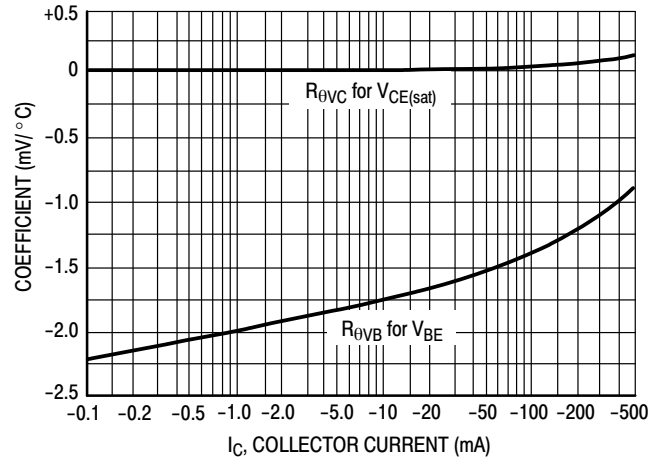


Figure 14. Temperature Coefficients

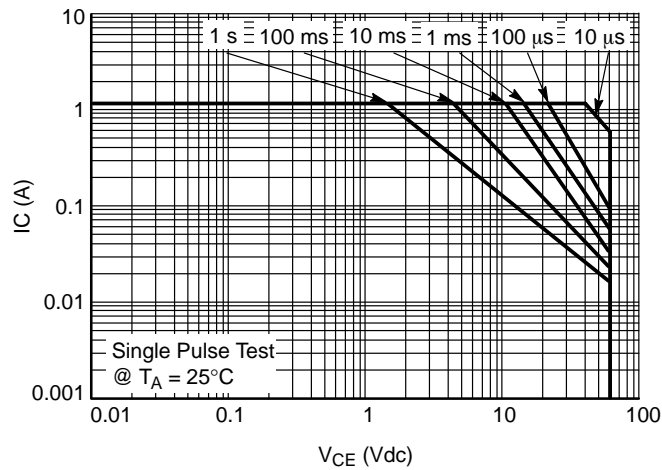


Figure 15. Safe Operating Area

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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### SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

### RECOMMENDED SOLDERING FOOTPRINT



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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